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APPLICATION NO.	FILING DATE	FIRST NAMED INVENTOR	ATTORNEY DOCKET NO.	CONFIRMATION NO.
10/786,151	02/26/2004	Mitsutoshi Miyasaka	118490	7277
25944	7590	08/19/2005		
OLIFF & BERRIDGE, PLC P.O. BOX 19928 ALEXANDRIA, VA 22320				
			EXAMINER ORTIZ, EDGARDO	
			ART UNIT	PAPER NUMBER
			2815	

DATE MAILED: 08/19/2005

Please find below and/or attached an Office communication concerning this application or proceeding.

**Office Action Summary**

Application No.

10/786,151

Applicant(s)

MIYASAKA, MITSUTOSHI

Examiner

Edgardo Ortiz

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-- The MAILING DATE of this communication appears on the cover sheet with the correspondence address --

**Period for Reply**

A SHORTENED STATUTORY PERIOD FOR REPLY IS SET TO EXPIRE 3 MONTH(S) FROM THE MAILING DATE OF THIS COMMUNICATION.

- Extensions of time may be available under the provisions of 37 CFR 1.136(a). In no event, however, may a reply be timely filed after SIX (6) MONTHS from the mailing date of this communication.
  - If the period for reply specified above is less than thirty (30) days, a reply within the statutory minimum of thirty (30) days will be considered timely.
  - If NO period for reply is specified above, the maximum statutory period will apply and will expire SIX (6) MONTHS from the mailing date of this communication.
  - Failure to reply within the set or extended period for reply will, by statute, cause the application to become ABANDONED (35 U.S.C. § 133).
- Any reply received by the Office later than three months after the mailing date of this communication, even if timely filed, may reduce any earned patent term adjustment. See 37 CFR 1.704(b).

**Status**

- 1) ☒ Responsive to communication(s) filed on 26 February 2004.
- 2a) ☐ This action is **FINAL**. 2b) ☒ This action is non-final.
- 3) ☐ Since this application is in condition for allowance except for formal matters, prosecution as to the merits is closed in accordance with the practice under *Ex parte Quayle*, 1935 C.D. 11, 453 O.G. 213.

**Disposition of Claims**

- 4) ☒ Claim(s) 1-13 is/are pending in the application.
- 4a) Of the above claim(s) \_\_\_\_\_ is/are withdrawn from consideration.
- 5) ☐ Claim(s) \_\_\_\_\_ is/are allowed.
- 6) ☒ Claim(s) 1-13 is/are rejected.
- 7) ☐ Claim(s) \_\_\_\_\_ is/are objected to.
- 8) ☐ Claim(s) \_\_\_\_\_ are subject to restriction and/or election requirement.

**Application Papers**

- 9) ☐ The specification is objected to by the Examiner.
- 10) ☐ The drawing(s) filed on \_\_\_\_\_ is/are: a) ☐ accepted or b) ☐ objected to by the Examiner.
- Applicant may not request that any objection to the drawing(s) be held in abeyance. See 37 CFR 1.85(a).
- Replacement drawing sheet(s) including the correction is required if the drawing(s) is objected to. See 37 CFR 1.121(d).
- 11) ☐ The oath or declaration is objected to by the Examiner. Note the attached Office Action or form PTO-152.

**Priority under 35 U.S.C. § 119**

- 12) ☒ Acknowledgment is made of a claim for foreign priority under 35 U.S.C. § 119(a)-(d) or (f).
- a) ☒ All b) ☐ Some \* c) ☐ None of:
1. ☒ Certified copies of the priority documents have been received.
2. ☐ Certified copies of the priority documents have been received in Application No. \_\_\_\_\_.
3. ☐ Copies of the certified copies of the priority documents have been received in this National Stage application from the International Bureau (PCT Rule 17.2(a)).

\* See the attached detailed Office action for a list of the certified copies not received.

**Attachment(s)**

- 1) ☒ Notice of References Cited (PTO-892)
- 2) ☐ Notice of Draftsperson's Patent Drawing Review (PTO-948)
- 3) ☒ Information Disclosure Statement(s) (PTO-1449 or PTO/SB/08)  
Paper No(s)/Mail Date 2/26/04.
- 4) ☐ Interview Summary (PTO-413)  
Paper No(s)/Mail Date. \_\_\_\_\_.
- 5) ☐ Notice of Informal Patent Application (PTO-152)
- 6) ☐ Other: \_\_\_\_\_.

## DETAILED ACTION

### *Claim Rejections - 35 USC § 112*

The following is a quotation of the second paragraph of 35 U.S.C. 112:

The specification shall conclude with one or more claims particularly pointing out and distinctly claiming the subject matter which the applicant regards as his invention.

1. Claim 4 rejected under 35 U.S.C. 112, second paragraph, as being indefinite for failing to particularly point out and distinctly claim the subject matter which applicant regards as the invention. Claim 4 refers to "*the channel region*" but it is unclear as to which channel region, namely that of the first conductivity type thin-film transistor or second conductivity type thin-film transistor Applicant is referring to.

### *Claim Rejections - 35 USC § 102*

The following is a quotation of the appropriate paragraphs of 35 U.S.C. 102 that form the basis for the rejections under this section made in this Office action:

A person shall be entitled to a patent unless –

(b) the invention was patented or described in a printed publication in this or a foreign country or in public use or on sale in this country, more than one year prior to the date of application for patent in the United States.

2. Claims 1-7 and 9-13 rejected under 35 U.S.C. 102(b) as being anticipated by Yamazaki et al. (U.S. Patent No. 5,858,823). With regard to Claim 1, Yamazaki discloses a complementary thin-film transistor circuit (column 1, lines 9-14), comprising:

a first conductivity type thin-film transistor and a second conductivity type thin-film transistor (P-Channel and N-Channel) formed using single crystal grains (121, 122) (column 14, lines 4 and figure 8B), the single crystal grains being formed substantially centered on each of a

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plurality of starting points (i.e. the center portion of each 121 and 122) disposed on an insulating surface of a substrate (10),

the first conductivity type thin-film transistor and the second conductivity type thin-film transistor formed in the single-crystal grains (121, 122) in which at least the channel regions the first conductivity type thin-film transistor and the second conductivity type thin-film transistor have the same plane orientation (figure 8B). It is noted that the limitation "formed by equalizing their drain current directions", is not a structural limitation that distinguishes the claimed invention from that disclosed by Yamazaki and thus was not given patentable weight.

With regard to Claim 2, Yamazaki discloses a first conductivity type thin-film transistor and a second conductivity type thin-film transistors (P-Channel and N-Channel) formed in one single crystal grain, since there is no grain boundary (column 4, lines 47-50) between single crystal grains (121, 122).

With regard to Claim 3, Yamazaki discloses electric field relief regions (17a, 17b) which are formed at both sides of the channel regions of the first conductivity type thin-film transistor and a second conductivity type thin-film transistors (P-Channel and N-Channel), the channel regions being sandwiched between the electric field relief regions, which are composed of low-concentration impurity regions, the electric field relief regions and the channel regions formed in the same single crystal grain (figure 8B).

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With regard to Claim 4, Yamazaki discloses a channel region formed in a region in the single crystal grain that does not include the starting point portion (i.e. the center portion of the single crystal grain) (see figure 12A).

With regard to Claim 5-6, it would have been obvious to modify the structure as disclosed by Yamazaki to pattern the single crystal grain in an U-shape or rectangular shape, since applicants have presented no explanation that these particular configurations of the single crystal grain are significant or are anything more than one of numerous configurations a person of ordinary skill in the art would find obvious for the purpose of providing a semiconductor layer for the purpose of forming transistor structures. A change in shape is generally recognizing as being within the level of ordinary skill in the art. *In re Dailey*, 149 USPQ 47 (CCPA 1976).

With regard to Claims 7 and 9-11, the claims contain limitations directed to process steps, which do not structurally or patentably distinguish the claimed invention from that disclosed by Yamazaki, the method of forming the device is not germane to the issue of patentability of the device itself.

With regard to Claims 12 and 13, Yamazaki discloses an electro-optical device or electronic apparatus comprising a complementary thin-film transistor as described by the reference in relation to claim 1, more specifically, the reference discloses a structure that is part of an active matrix display type liquid crystal display (column 13, lines 20-27).

***Claim Rejections - 35 USC § 103***

The following is a quotation of 35 U.S.C. 103(a) which forms the basis for all obviousness rejections set forth in this Office action:

(a) A patent may not be obtained though the invention is not identically disclosed or described as set forth in section 102 of this title, if the differences between the subject matter sought to be patented and the prior art are such that the subject matter as a whole would have been obvious at the time the invention was made to a person having ordinary skill in the art to which said subject matter pertains. Patentability shall not be negated by the manner in which the invention was made.

3. Claim 8 rejected under 35 U.S.C. 103(a) as being unpatentable over Yamazaki et al. (U.S. Patent No. 5,858,823) in view of Ishihara et al. ("Advanced Excimer-Laser Crystallization Techniques of Si Thin-Film For Location Control of Large Grain on Glass", Proceeding of SPIE, Vol. 4295, Pages 14-23, 2001). With regard to Claim 8, Yamazaki essentially discloses the claimed invention but fails to disclose the claimed starting-point portion being a concave portion formed on an insulating substrate. However, Ishihara discloses a crystallization method in which a concave portion is formed on an insulating substrate which acts as a starting point for the crystallization (see page 19, under section 3.2 "Grain-Filter Process"). Therefore, it would have been obvious to someone with ordinary skill in the art, at the time of the invention, to modify the structure as disclosed by Yamazaki to include the claimed starting-point portion being a concave portion formed on an insulating substrate, as suggested by Ishihara, since allows for an irradiation process with an energy higher than that for a complete melting of the thin-film silicon film, thus more heat can be introduced in the film, and the cooling rate at the onset of solidification of the film will be reduced so that lateral growth can be continued longer.

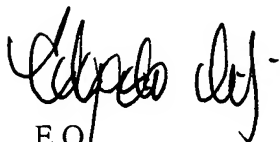
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***Conclusion***

4. Any inquiry concerning this communication or earlier communications from the examiner should be directed to Edgardo Ortiz whose telephone number is 571-272-1735. The examiner can normally be reached on Monday-Friday (1st Friday Off).

If attempts to reach the examiner by telephone are unsuccessful, the examiner's supervisor, Tom Thomas can be reached on 571-272-1664. The fax phone number for the organization where this application or proceeding is assigned is 703-872-9306.

Information regarding the status of an application may be obtained from the Patent Application Information Retrieval (PAIR) system. Status information for published applications may be obtained from either Private PAIR or Public PAIR. Status information for unpublished applications is available through Private PAIR only. For more information about the PAIR system, see <http://pair-direct.uspto.gov>. Should you have questions on access to the Private PAIR system, contact the Electronic Business Center (EBC) at 866-217-9197 (toll-free).



E.O.  
A.U. 2815  
8/18/05



**JEROME JACKSON  
PRIMARY EXAMINER**